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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HSM83

Silicon Epitaxial Planar Diode for High Voltage Switching

RENESAS

ADE-208-091D(Z)

Rev. 4
Jun. 1996

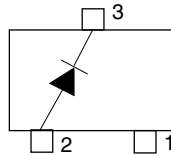
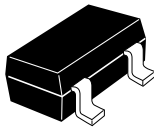
Features

- High reverse voltage. ($V_R = 250V$)
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM83	F7	MPAK

Pin Arrangement



(Top View)

- 1 NC
- 2 Anode
- 3 Cathode

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	300	V
Reverse voltage	V_R	250	V
Peak forward current	I_{FM}	300	mA
Non-Repetitive peak forward surge current	I_{FSM}^{*1}	2	A
Average rectified current	I_O	100	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note: 1. Value at duration of 10msec.

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.2	V	$I_F = 100 \text{ mA}$
Reverse current	I_{R1}	—	—	0.2	μA	$V_R = 250\text{V}$
	I_{R2}	—	—	100		$V_R = 300\text{V}$
Capacitance	C	—	1.5	3.0	pF	$V_R = 0\text{V}$, $f = 1 \text{ MHz}$
Reverse recovery time	t_{rr}	—	—	100	ns	$I_F = I_R = 30 \text{ mA}$, $I_{rr} = 3\text{mA}$, $R_L = 100\Omega$

Main Characteristic

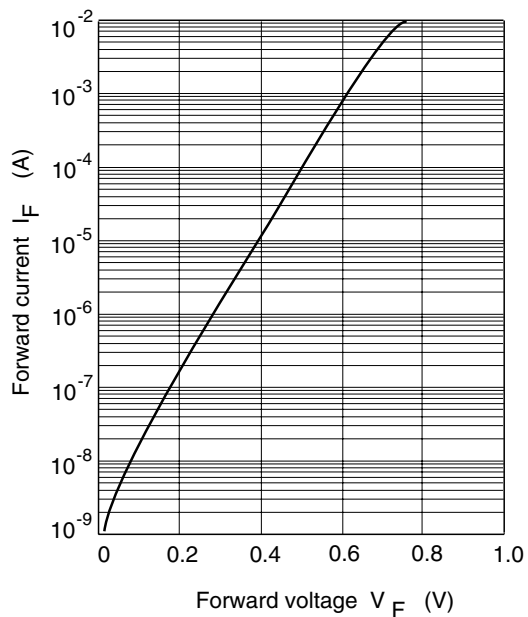


Fig.1 Forward current Vs. Forward voltage

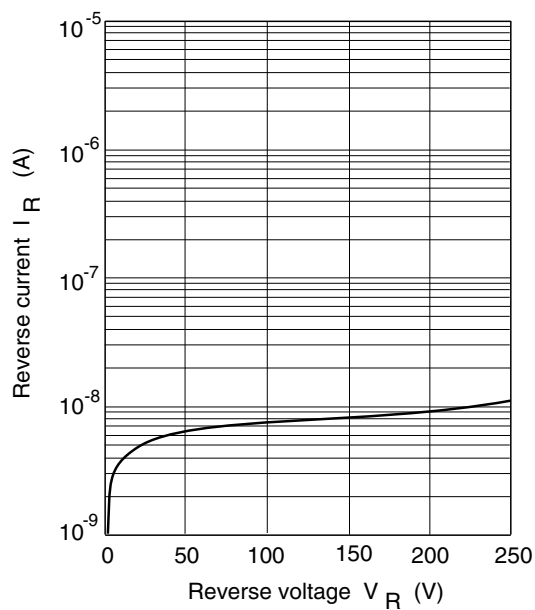


Fig.2 Reverse current Vs. Reverse voltage

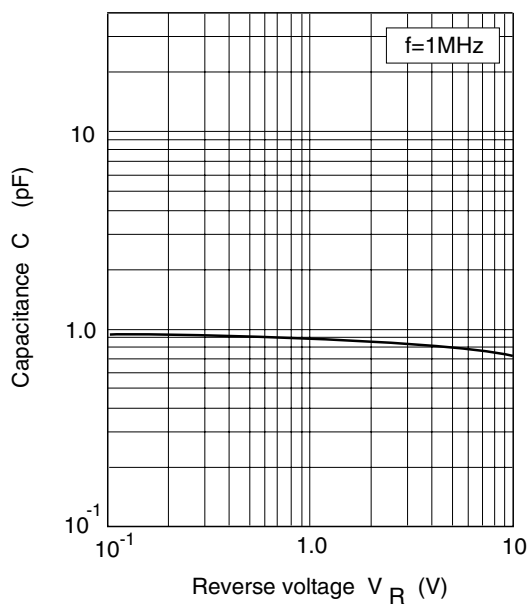
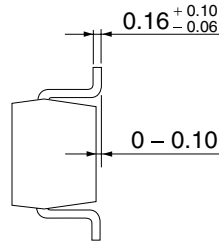
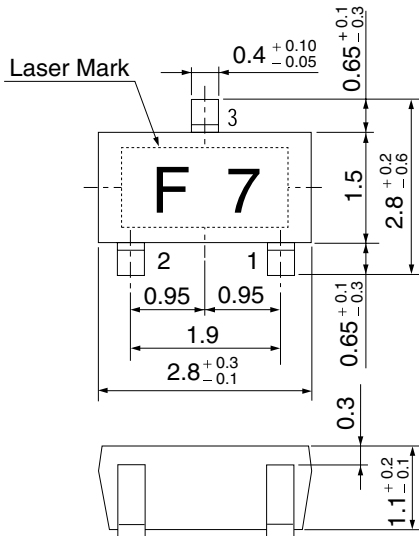


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



- 1 NC
- 2 Anode
- 3 Cathode

Hitachi Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011

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